

## UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Vingnia 22313-1450 www.nepto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/900,043	07/09/2001	Takahiro Yajima	35.C15541	3915
5514 75	590 06/17/2003			
FITZPATRICK CELLA HARPER & SCINTO			EXAMINER	
30 ROCKEFEL NEW YORK, N			DANG, T	RUNG Q
			ART UNIT	PAPER NUMBER
			2823	
			DATE MAILED: 06/17/2003	3

Please find below and/or attached an Office communication concerning this application or proceeding.

.;	-	Application No.	Applicant(s)	- <del>(Vv</del>
•*	_	09/900,043	YAJIMA ET AL.	
	Office Action Summary	Examiner	Art Unit	
		Trung Q. Dang	2823	
	The MAILING DATE of this communica			ss
Period fo	or Reply			
THE   - Exte after - If the - If NC - Failu - Any i	ORTENED STATUTORY PERIOD FOR MAILING DATE OF THIS COMMUNICA naions of time may be available under the provisions of 3 SIX (6) MONTHS from the mailing date of this communical period for reply specified above is less than thirty (30) of period for reply is specified above, the maximum statuture to reply within the set or extended period for reply will reply received by the Office later than three months after adaptant term adjustment. See 37 CFR 1.704(b).	ATION.  37 CFR 1.136(a). In no event, however, may a cation.  lays, a reply within the statutory minimum of the complete of th	n reply be timely filed irty (30) days will be considered timely. INTHS from the mailing date of this comm ABANDONED (35 U.S.C. § 133).	unication.
1)	Responsive to communication(s) filed	on		
2a) <u></u> □	This action is <b>FINAL</b> . 2b	)⊠ This action is non-final.		
3) Disposit	Since this application is in condition for closed in accordance with the practice ion of Claims			nerits is
4) 🖂	Claim(s) 1-10 is/are pending in the ap	plication.	,	
	4a) Of the above claim(s) is/are	withdrawn from consideration.		•
5)🖂	Claim(s) 6-10 is/are allowed.			
6)⊠	Claim(s) <u>1-5</u> is/are rejected.			
7)	Claim(s) is/are objected to.		•	
8) 🗌	Claim(s) are subject to restrictio	n and/or election requirement.		
Applicati	on Papers			
9) 🗌 .	The specification is objected to by the E	xaminer.		
10) 🔲	The drawing(s) filed on is/are: a)	☐ accepted or b)☐ objected to by	the Examiner.	
—	Applicant may not request that any object	- · · ·	•	
11) 📙 .	The proposed drawing correction filed o		disapproved by the Examiner.	
40.	If approved, corrected drawings are require	• •	•	
	The oath or declaration is objected to by	/ the Examiner.		
	ınder 35 U.S.C. §§ 119 and 120			
· .	Acknowledgment is made of a claim for	r foreign priority under 35 U.S.C.	§ 119(a)-(d) or (f).	
a)[	⊠ All b) ☐ Some * c) ☐ None of:			
	1. Certified copies of the priority do			
	2. Certified copies of the priority do			
* S	3. Copies of the certified copies of the application from the Internation from the attached detailed Office action for the attached detailed	onal Bureau (PCT Rule 17.2(a)).		ge
14) 🗌 A	cknowledgment is made of a claim for c	domestic priority under 35 U.S.C	. § 119(e) (to a provisional ap	plication).
	☐ The translation of the foreign langu Acknowledgment is made of a claim for o	<del>-</del> •		
Attachment	(s)			
2) Notice	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO- nation Disclosure Statement(s) (PTO-1449) Paper	-948) 5) Notice of	Summary (PTO-413) Paper No(s) Informal Patent Application (PTO-15	
S. Patent and Tr TO-326 (Re		Office Action Summary	Part of Paper No. 12	

Application/Control Number: 09/900,043 Page 2

Art Unit: 2823

1. The indicated allowability of claims 1-5 is withdrawn in view of the newly discovered reference(s) to Li et al (U.S. Pat. 5,942,049) and Otani et al. (EP 658918), all cited by applicants. Rejections based on the newly cited reference(s) follow.

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-5 are rejected under 35 U.S.C. 103(a) as being unpatentable over Li et al. In view of Otani et al.

Li teaches a method for depositing an amorphous silicon film by plasma CVD in a RF glow-discharge system. The reactive gases disclosed are SiH4, H2 (see Table 7 and 8 for the flow rate of SiH4 and hydrogen dilution ratio). The deposition pressure P and electrode spacing d are disclosed in Table 7. From Table 8, selecting a value for the flow rate of SiH4 of 60 sccm (0.06 SLM) within the disclosed range. Accordingly, the flow rate M of H2 is 600 sccm (0.6 SLM) when the hydrogen dilution ratio of 10:1 is selected according to Table 7. From Table 7, selecting a value of 2 torr (approximately 266 Pa) for pressure P and a value of 1cm electrode spacing d. Substitute these values in the equation recited in the pending claim 1 yields:

Application/Control Number: 09/900,043 Page 3

Art Unit: 2823

$$80 (0.6) + 200 \le 266.1 \le 160 (0.6) + 333$$
  
 $248 \le 266 \le 429$ 

Thus, with respect to the relation as claimed, Li teaching satisfy the equation claimed in claim 1. Li differs from the claims in not disclosing that the substrate is employed as one electrode in the RF glow-discharge apparatus. However, Otani teaches a RF plasma - CVD reactors with internal electrodes wherein substrate S1 is mounted on electrode 2 and hence employed as one of electrode opposite to RF electrode 3 (see Fig. 1). Thus, it would have been obvious to one of ordinary skill in the art to mount the substrate in Li's process on one of the electrode in the RF plasma-CVD reactor as suggested by Otani because such practice is conventional in the art, and the application of a known technique to make the same would have been within the level of an artisan. As for claim 2, substituting the values of P, d, and L (total flow rates of SiH4 and H2 = 0.6 SLM + 0.06 SLM = 0.66 SLM) to the equation yields:

$$67 (0.66) + 200 \le 266 \le 147 (0.66) + 333$$
  
 $244 \le 266 \le 430$ 

Thus, claim 2 is met by Li.

3. The following is an examiner's statement of reasons for allowance:

Claims 6-10 are allowable over prior art of record because none of prior art teaches or suggests the relation as claimed, which involves volume V of the discharge space.

Application/Control Number: 09/900,043

Page 4

Art Unit: 2823

Any comments considered necessary by applicant must be submitted no later than the

payment of the issue fee and, to avoid processing delays, should preferably accompany the issue

fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for

Allowance."

4. Any inquiry concerning this communication or earlier communications from the examiner

should be directed to Trung Dang whose telephone number is (703) 308-2548. The examiner can

normally be reached on weekdays from 9:00 AM to 5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor,

Olik Chaudhuri, can be reached on (703) 306-2794. The fax phone number for this Group is

(703) 305-3432 or (703) 308-7725.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the Group receptionist whose telephone number is (703) 308-0956.

Trung Dang

Primary Examiner, Group 2800